**Philips Semiconductors** 

**Product specification** 

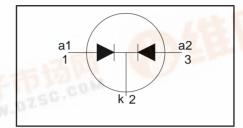
## Rectifier diodes Schottky barrier

## PBYR645CT series

### **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

### **SYMBOL**



### QUICK REFERENCE DATA

$$V_R = 35 \text{ V}/ 40 \text{ V}/ 45 \text{ V}$$
 $I_{O(AV)} = 10 \text{ A}$ 
 $V_F \le 0.6 \text{V}$ 

### **GENERAL DESCRIPTION**

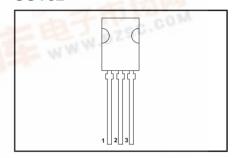
Dual, common cathode schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR645CT series is supplied in the conventional leaded SOT82 package.

### **PINNING**

PIN	DESCRIPTION	
1	anode 1	
2	cathode	
3	anode 2	
tab	cathode	

### SOT82



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	27	MAX.	0.00	UNIT
$V_{RRM}$	Peak repetitive reverse	PBYR6		<b>35CT</b> 35	<b>40CT</b> 40	<b>45CT</b> 45	V
V RRM	voltage				10	10	
$V_{RWM}$	Working peak reverse voltage	TO TO	-	35	40	45	V
$V_R$	Continuous reverse voltage	T <sub>mb</sub> ≤ 100 °C	-	35	40	45	V
I <sub>O(AV)</sub>	Average rectified output current (both diodes conducting)	square wave; $\delta = 0.5$ ; $T_{mb} \le 119$ °C	-		10		А
I <sub>FRM</sub>	Repetitive peak forward current per diode	square wave; $\delta = 0.5$ ; $T_{mb} \le 119$ °C	-		10		Α
I <sub>FSM</sub>	Non-repetitive peak forward current diode	t = 10  ms t = 8.3  ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$		NWW	75 82		A A
I <sub>RRM</sub>	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T <sub>i max</sub>	-		1		Α
T <sub>j</sub>	Operating junction temperature	CG.COM	-		150		°C
$T_{stg}$	Storage temperature	==	- 65		150		°C

### THERMAL RESISTANCES

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	to mounting base	per diode both diodes in free air	1 1 1	- - 100	5 4 -	K/W K/W K/W

Rectifier	diodes
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# **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage	$I_{\rm F} = 5 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.51	0.6	V
		$I_{\rm F} = 10  {\rm A}^{-3}$	-	0.72	0.87	V
I <sub>R</sub>	Reverse current	$\dot{V}_R = V_{RWM}$	-	0.12	0.5	mΑ
		$V_{R} = V_{RWM}; T_{i} = 100^{\circ}C$	-	10	15	mΑ
C <sub>d</sub>	Junction capacitance	$V_{R} = 5 \text{ V}$ ; $f = 1 \text{ MHz}$ , $T_{i} = 25 ^{\circ}\text{C}$ to $125 ^{\circ}\text{C}$	-	150	-	pF

# Rectifier diodes Schottky barrier

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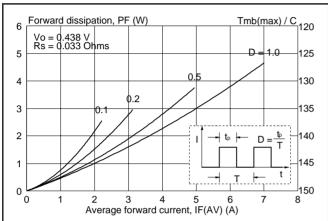


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$ .

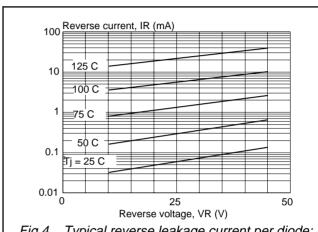


Fig.4. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_j$ 

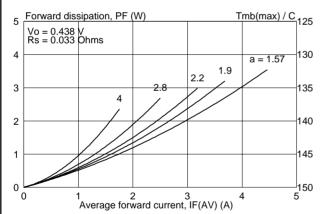


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = f form factor  $= I_{F(RMS)} / I_{F(AV)}$ .

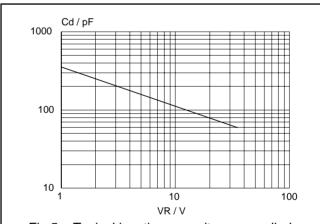


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125 °C.

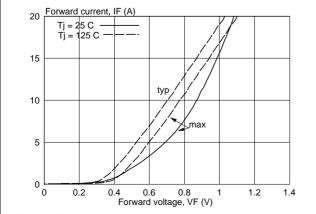


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 

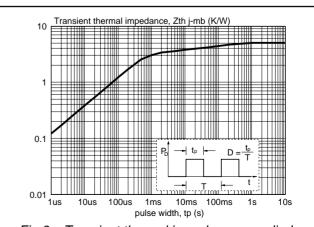
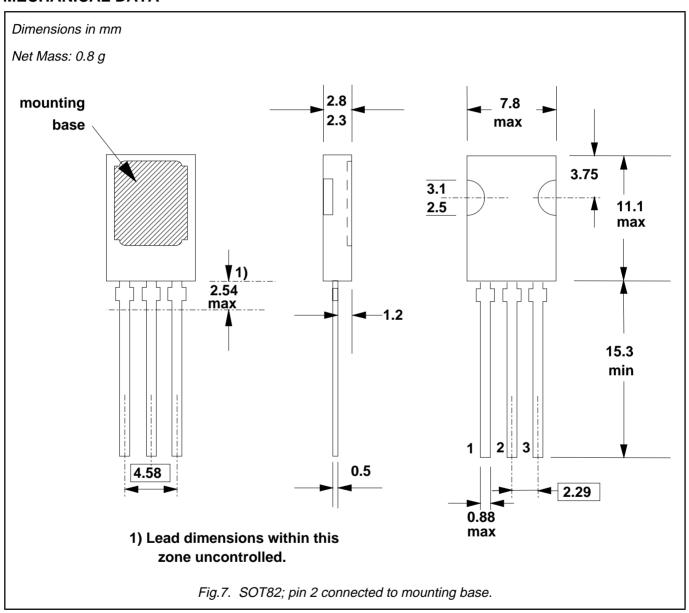


Fig.6. Transient thermal impedance; per diode;  $Z_{th j - mb} = f(t_p)$ .

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### **MECHANICAL DATA**



### **Notes**

- Refer to mounting instructions for SOT82 envelopes.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier	diodes
Schottky	barrier

PBYR645CT series

### **DEFINITIONS**

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la				
Product specification This data sheet contains final product specifications.				
Limiting values				

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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